

## AMENDMENTS TO THE CLAIMS

The following is a complete, marked up listing of revised claims with a status identifier in parentheses, underlined text indicating insertions, and strikethrough and/or double-bracketed text indicating deletions.

### LISTING OF CLAIMS

1. (PREVIOUSLY PRESENTED) A field-effect transistor, comprising:

a ferromagnetic layer, having a film thickness of 50 nm or less, which is made of a Ba-Mn oxide showing ferromagnetism at 0°C or higher;

a dielectric layer made of a dielectric material or a ferroelectric material, said ferromagnetic layer and said dielectric layer being bonded to each other, wherein the field-effect transistor has a bottom-gate structure.

2. (ORIGINAL) The field-effect transistor as set forth in claim 1, wherein the ferromagnetic layer is made of a Ba-Mn oxide whose composition is represented by  $(La_{1-x}Ba_x)MnO_3$  where x satisfies  $0.05 < x < 0.3$ .

3. (ORIGINAL) The field-effect transistor as set forth in claim 1, wherein the ferromagnetic layer is made of a Ba-Mn oxide whose composition is represented by  $(La_{1-x}Ba_x)MnO_3$  where x satisfies  $0.10 < x < 0.3$ .

4. (CURRENTLY AMENDED) The field-effect transistor as set forth in claim 1, wherein the dielectric material or the ferroelectric material is  $\text{BaTiO}_3$ ,  $\text{SrTiO}_3$ ,  $(\text{Ba}_{1-y}\text{Sr}_y)\text{TiO}_3$ ,  $\text{PbTiO}_3$ ,  ~~$\text{Pb}(\text{Zr}_{1-z}\text{Ti}_z)\text{TiO}_3$~~ ,  $\text{Pb}(\text{Zr}_{1-z}\text{Ti}_z)\text{O}_3$ , or  $\text{Al}_2\text{O}_3$ , where y satisfies  $0 < y < 1$  and z satisfies  $0 < z < 1$ .

5. (PREVIOUSLY PRESENTED) The field-effect transistor as set forth in claim 1, wherein the dielectric material or the ferroelectric material is  $\text{BaTiO}_3$ ,  $\text{SrTiO}_3$ ,  $(\text{Ba}_{1-y}\text{Sr}_y)\text{TiO}_3$ ,  $\text{PbTiO}_3$ , or  $\text{Al}_2\text{O}_3$ , where y satisfies  $0 < y < 1$ .

6. (CANCELLED)

7. (CURRENTLY AMENDED) The field-effect transistor as set forth in claim 2, wherein the dielectric material or the ferroelectric material is  $\text{BaTiO}_3$ ,  $\text{SrTiO}_3$ ,  $(\text{Ba}_{1-y}\text{Sr}_y)\text{TiO}_3$ ,  $\text{PbTiO}_3$ ,  ~~$\text{Pb}(\text{Zr}_{1-z}\text{Ti}_z)\text{TiO}_3$~~ ,  $\text{Pb}(\text{Zr}_{1-z}\text{Ti}_z)\text{O}_3$ , or  $\text{Al}_2\text{O}_3$ , where y satisfies  $0 < y < 1$  and z satisfies  $0 < z < 1$ .

8. (PREVIOUSLY PRESENTED) The field-effect transistor as set forth in claim 2, wherein the dielectric material or the ferroelectric material is  $\text{BaTiO}_3$ ,  $\text{SrTiO}_3$ ,  $(\text{Ba}_{1-y}\text{Sr}_y)\text{TiO}_3$ ,  $\text{PbTiO}_3$ , or  $\text{Al}_2\text{O}_3$ , where y satisfies  $0 < y < 1$ .

9. (CURRENTLY AMENDED) The field-effect transistor as set forth in claim 3, wherein the dielectric material or the ferroelectric material is  $\text{BaTiO}_3$ ,  $\text{SrTiO}_3$ ,  $(\text{Ba}_{1-y}\text{Sr}_y)\text{TiO}_3$ ,  $\text{PbTiO}_3$ ,

~~Pb~~ ~~(Zr<sub>1-z</sub>Ti<sub>z</sub>)TiO<sub>3</sub>~~ Pb(Zr<sub>1-z</sub>Ti<sub>z</sub>)O<sub>3</sub>, or Al<sub>2</sub>O<sub>3</sub>, where y satisfies 0<y<1 and z satisfies 0<z<1.

10. (PREVIOUSLY PRESENTED) The field-effect transistor as set forth in claim 3, wherein the dielectric material or the ferroelectric material is BaTiO<sub>3</sub>, SrTiO<sub>3</sub>, (Ba<sub>1-y</sub>Sr<sub>y</sub>)TiO<sub>3</sub>, PbTiO<sub>3</sub>, or Al<sub>2</sub>O<sub>3</sub>, where y satisfies 0<y<1.